



AMDU040N020PSVRH

Single N-channel Trench MOSFET 40V 2.07mΩ

FEATURES

- Trench power MOSFET technology
- Single N-channel trench, normal gate level
- Enhanced avalanche ruggedness
- 100% Avalanche tested
- Maximum 175°C junction temperature

PRODUCT VALIDATION

- Qualified according to AEC-Q101 Standard

KEY PERFORMANCE PARAMETERS

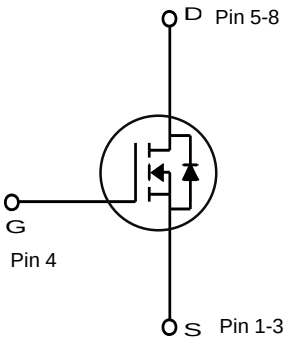
V_{DS}	40	V
$R_{DS(on), typ.}$	0.00177	Ω
I_D	146	A
Q_g	29	nC
Junction temperature, max	175	$^{\circ}C$



Top View



Bottom View



RoHS Compliant
HALOGEN-FREE



ORDERING INFORMATION

Type / Ordering Code	Package	Marking	Packing	RoHS Status
AMDU040N020PSVRH	PDFN56	040N020P	Tape & Reel	Halogen Free

<http://www.magnachip.com/>

ABSOLUTE MAXIMUM RATINGS, at $T_C = 25^{\circ}\text{C}$, unless otherwise specified

Parameter		Symbol	Rating	Unit
Drain-source Voltage		V_{DS}	40	V
Gate-source Voltage		V_{GS}	± 20	
Drain current	$T_C=25^{\circ}\text{C}$ (Silicon Limited)	I_D	146	A
	$T_C=25^{\circ}\text{C}$ (Package Limited)		135	
	$T_C=100^{\circ}\text{C}$ (Silicon Limited)		103	
¹⁾ Pulsed drain current	$T_C=25^{\circ}\text{C}$, $t_p \leq 100 \mu\text{s}$	I_{DM}	582	
Total power dissipation	$T_C=25^{\circ}\text{C}$	P_{tot}	75	W
	$T_C=100^{\circ}\text{C}$		38	
²⁾ Avalanche energy, single pulse		E_{AS}	122	mJ
Operating and storage temperature		T_J, T_{stg}	- 55 ~ 175	$^{\circ}\text{C}$

THERMAL CHARACTERISTICS

Parameter	Symbol	Rating	Unit
Thermal resistance, junction - case	$R_{\theta JC}$	2	K/W
³⁾ Thermal resistance, junction - ambient	$R_{\theta JA}$	50	

ELECTRICAL CHARACTERISTICS (T_j = 25°C)**STATIC CHARACTERISTICS**

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions / Note
Drain-source breakdown voltage	V _{(BR)DSS}	40	-	-	V	V _{GS} =0 V, I _D =250 μA
Gate threshold voltage	V _{GS(th)}	2.25	-	3.75		V _{DS} =V _{GS} , I _D =171 μA
Zero gate voltage drain current	I _{DSS}	-	-	1	μA	V _{DS} =40 V, V _{GS} =0 V
Gate-source leakage current	I _{GSS}	-	-	± 100	nA	V _{GS} =±20 V, V _{DS} =0 V
Drain-source on-state resistance	R _{DS(on)}	-	1.77	2.07	mΩ	V _{GS} =10 V, I _D =50 A
		-	1.90	2.40		V _{GS} =8 V, I _D =50 A
⁴⁾ Gate resistance	R _g	-	2.3	-	Ω	f=1 MHz
⁴⁾ Transconductance	g _{fs}	-	90	-	S	V _{DS} =10 V, I _D =50 A

⁴⁾ DYNAMIC CHARACTERISTICS

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions / Note
Input capacitance	C _{iss}	-	2201	-	pF	V _{GS} =0 V, V _{DS} =20 V, f=1 MHz
Output capacitance	C _{oss}	-	599	-		
Reverse transfer capacitance	C _{rss}	-	27	-		
Turn-on delay time	t _{d(on)}	-	20	-	ns	V _{DD} =20 V, V _{GS} =10 V, I _D =50 A, R _{G,ext} =3 Ω
Rise time	t _r	-	5	-		
Turn-off delay time	t _{d(off)}	-	35	-		
Fall time	t _f	-	10	-		

⁴⁾ GATE CHARGE CHARACTERISTICS

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions / Note
Gate to source charge	Q _{gs}	-	10	-	nC	V _{DD} =32 V, I _D =50 A, V _{GS} =0 to 10 V
Gate charge at threshold	Q _{gs(th)}	-	6	-		
Gate to drain charge	Q _{gd}	-	5	-		
Switching charge	Q _{sw}	-	9	-		
Gate charge total	Q _g	-	29	-		
Gate plateau voltage	V _{plateau}	-	5.1	-	V	

SOURCE-DRAIN DIODE

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions / Note
⁴⁾ Diode continuous forward current	I _S	-	-	135	A	-
⁴⁾ Diode pulse current	I _{S,pulse}	-	-	582	A	pulsed; t _p ≤ 100 μs
Diode forward voltage	V _{SD}	-	0.8	1.1	V	V _{GS} =0 V, I _F =50 A
⁴⁾ Reverse recovery time	t _{rr}	-	32	-	ns	I _F =50 A, di _F /dt=100 A/μs
⁴⁾ Reverse recovery charge	Q _{rr}	-	11	-	nC	

Notes

1. Pulse width limited by T_{jmax}
2. Starting T_j=25°C, L=1mH, I_{AS}=15.6A, V_{DD}=36V, V_{GS}=10V
3. Surface mounted FR-4 board by JEDEC (jesd51-7)
4. The parameter is not subject to production testing - guaranteed by design.

ELECTRICAL CHARACTERISTICS DIAGRAMS (25 °C, unless otherwise noted)

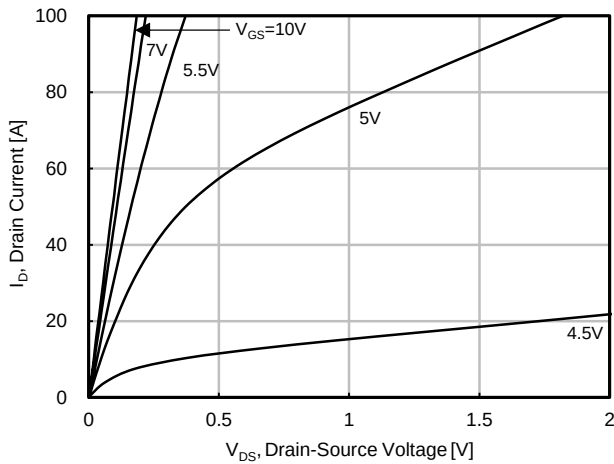


Fig. 1. Typ. Output Characteristics

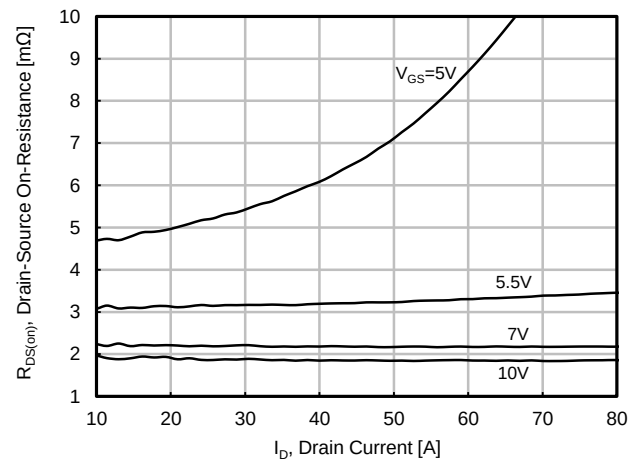


Fig. 2. Typ. Drain to Source On-Resistance

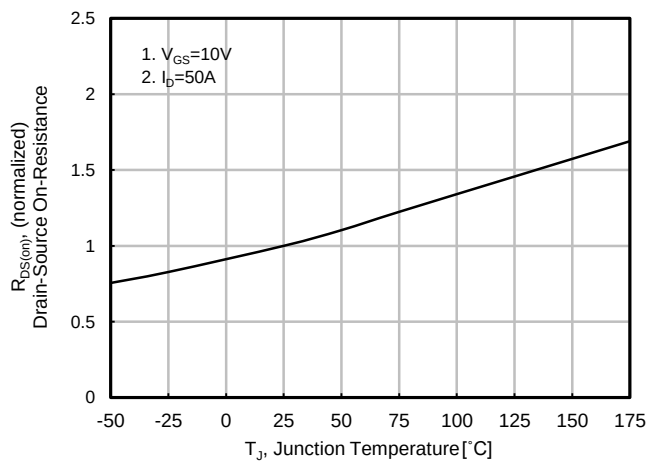


Fig. 3. On-Resistance vs. Junction Temperature

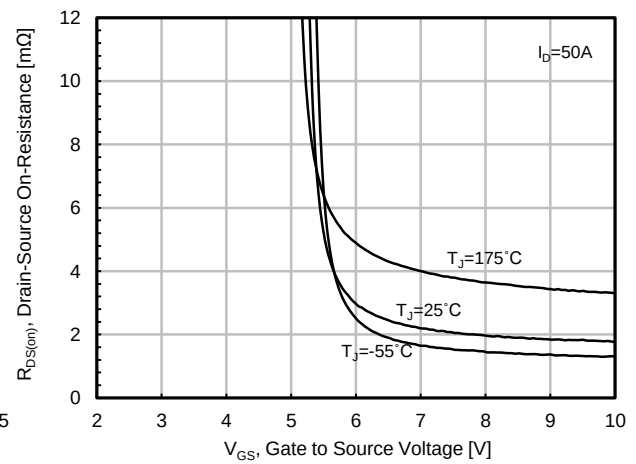


Fig. 4. On-Resistance vs. Gate to Source Voltage

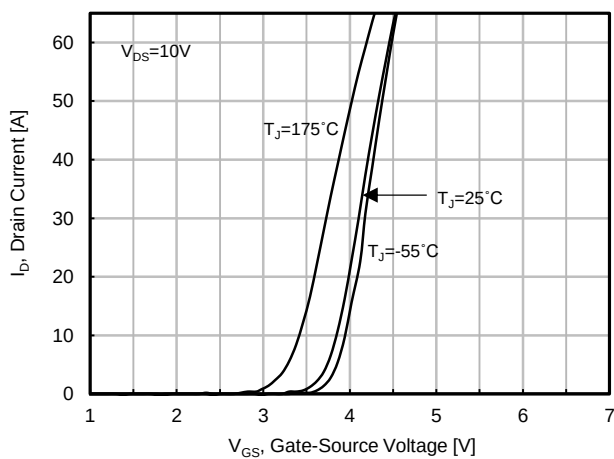


Fig. 5. Typ. Transfer Characteristics

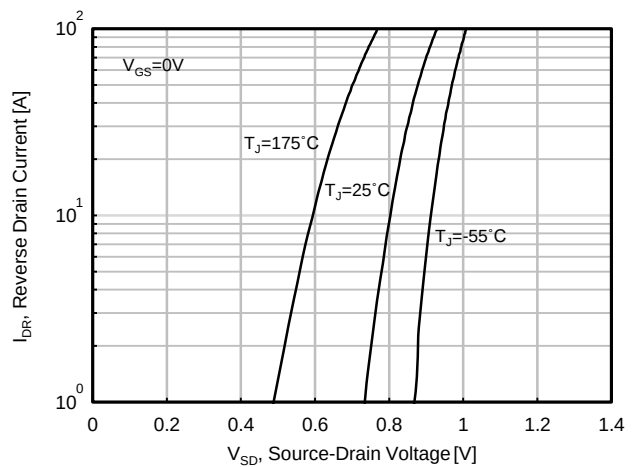
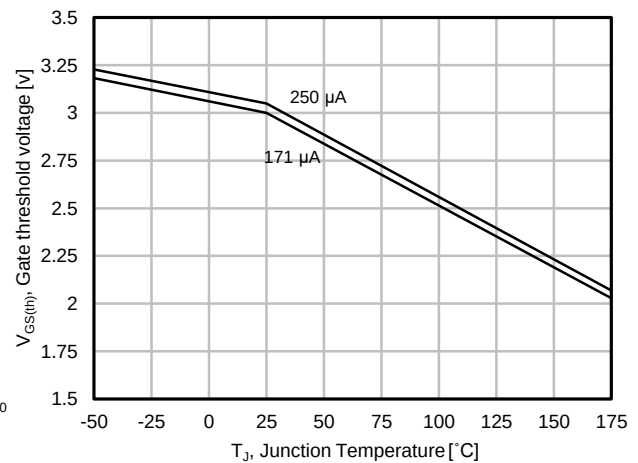
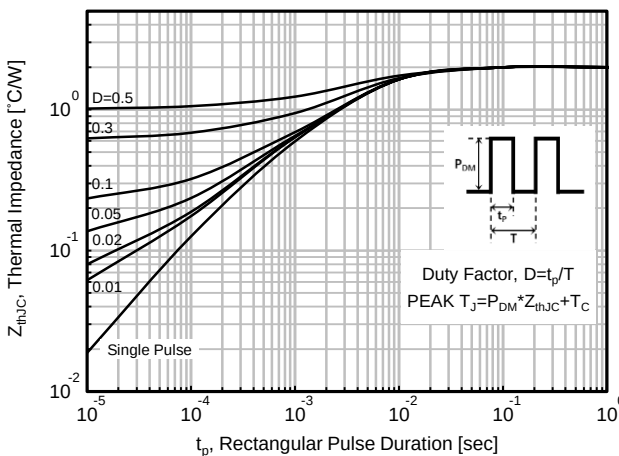
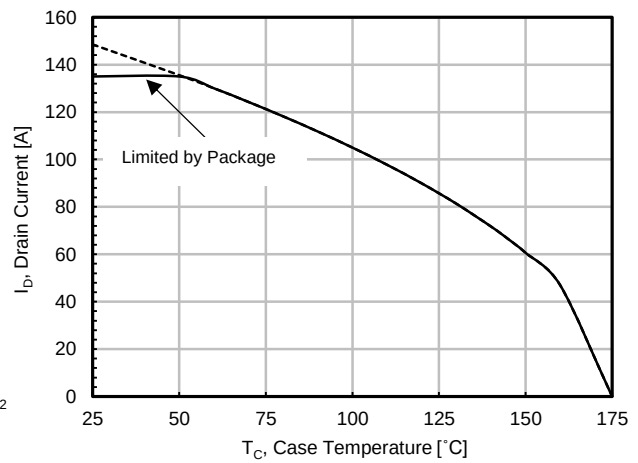
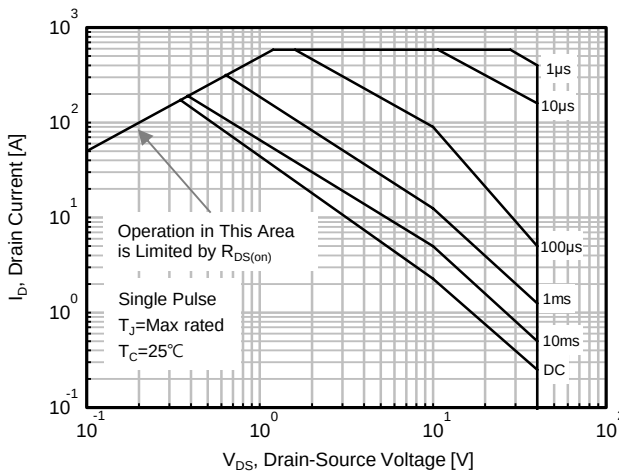
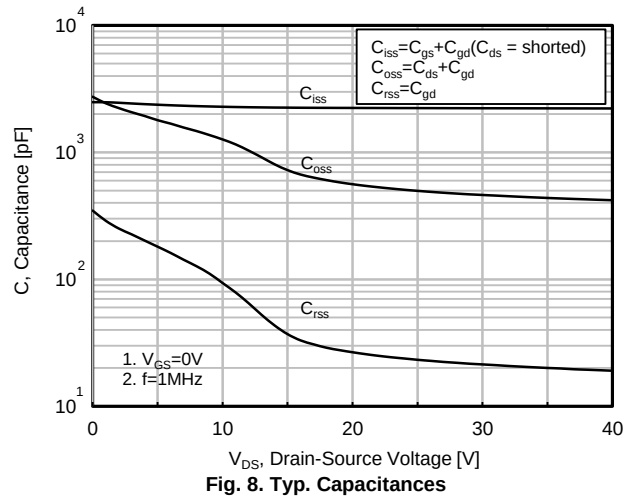
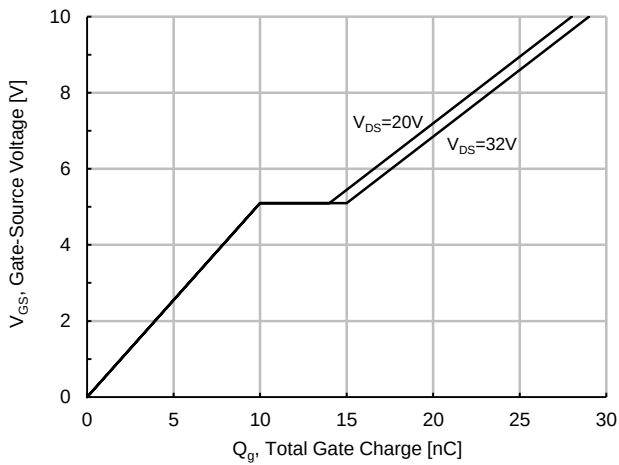
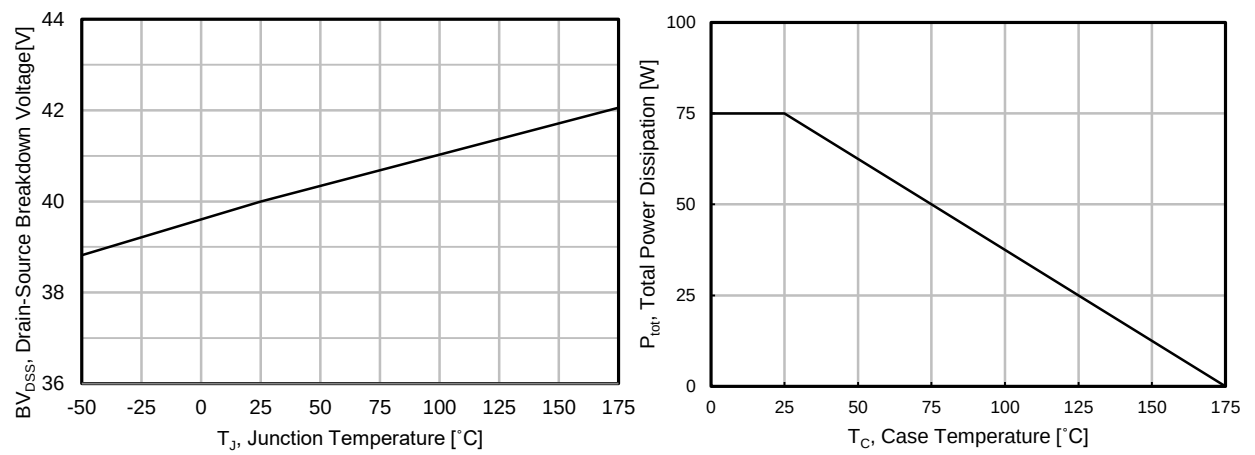


Fig. 6. Forward Characteristics of Reverse Diode

ELECTRICAL CHARACTERISTICS DIAGRAMS (25 °C, unless otherwise noted)

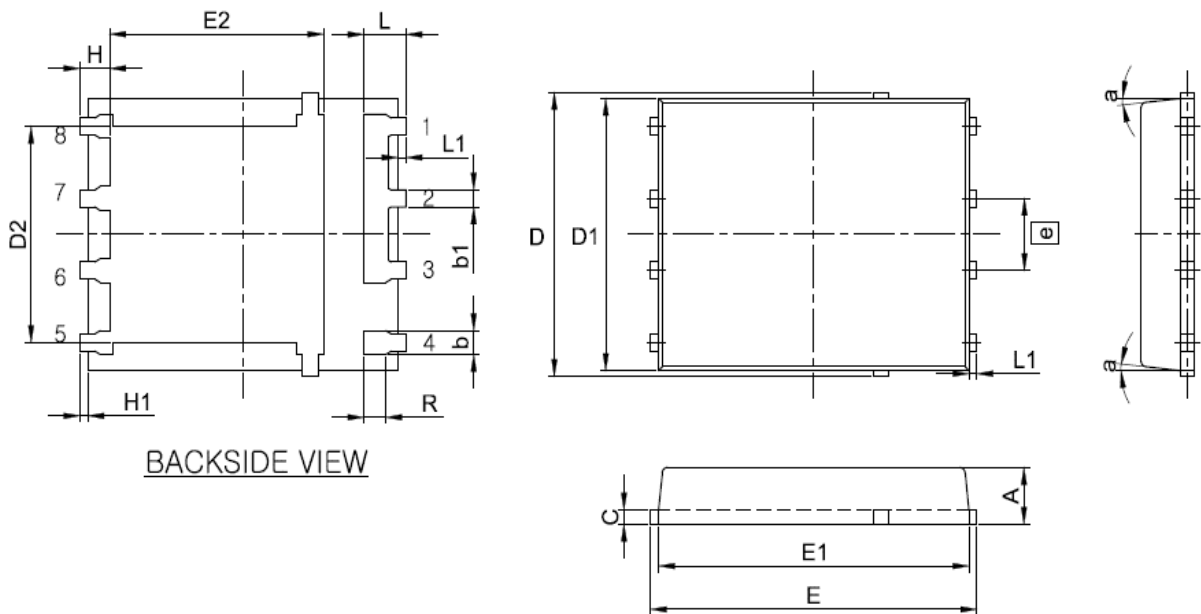


ELECTRICAL CHARACTERISTICS DIAGRAMS (25 °C, unless otherwise noted)



Package Outlines

PDFN56



Symbol	Dimension (mm)		
	Min	Nom	Max
A	0.90	–	1.10
b	0.33	–	0.49
b1	0.26	–	1.36
C	0.20	0.25	0.34
D	4.50	5.15	5.30
D1	4.50	5.00	5.10
D2	3.65	–	3.95
E	5.90	6.15	6.30
E1	5.85	6.00	6.10
E2	3.46	–	3.86
e	1.27 BSC		
H	0.50	–	0.71
H1	0.03	–	0.13
L	0.74	–	0.84
L1	0.03	–	0.13
R	0.48	–	0.58
a	0°	–	12°

Notes
Package body size, length and width do not include mold flash, protrusions and gate burrs.

DISCLAIMER :

The Products are not designed for use in hostile environments, including, without limitation, aircraft, nuclear power generation, medical appliances, and devices or systems in which malfunction of any Product can reasonably be expected to result in a personal injury. Seller's customers using or selling Seller's products for use in such applications do so at their own risk and agree to fully defend and indemnify Seller.

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